

# Integrated Molecular Beam Epitaxy System Model IMBE300-B

Epitaxial Growth Process with integrated monitoring, 2-D crystallography, composition and electronics band analysis in one UHV chamber.



Basic MBE System Configuration

## TECHNIQUES:

- LEED (Low Energy Electron Diffraction)
- AES (Auger Electron Spectroscopy)
- Thin Film Thickness Monitor
- 7 Deposition Sources

## Available Ports:

- XPS (X-Ray Photoelectron Spectroscopy)
- RHEED (Reflection High Energy Electron Diffraction)
- TDS (Thermal Desorption Mass Spectroscopy)

## FEATURES:

- No need to transfer to another UHV chamber for analysis after film growth
- Short switching time between deposition and surface science analysis
- Load-lock with transfer arm and sample storage
- Sample transfer compatibility with other systems: SPM and SEM